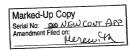
208954US-2RD CONT



IN THE SPECIFICATION

To realize such good close-packed plane orientation, the spin valve films may be

Page 109, beginning at line 21, please delete the paragraph and replace it with the following new paragraph:

formed in an atmosphere with impurities such as oxygen gas and others therein being minimized as much as possible. For example, for forming the films, employable are a deposition method in which is used an apparatus capable of pre-degassing the system to a level or around 10° Torr; a deposition method in which is used a sputtering target of which the oxygen content is lowered to at most 500 ppm; a substrate bias sputtering method in which a controlled degree of energy is applied to the sputtered atoms while the atoms are deposited on the substrate; and a deposition method in which a underlayer of a simple noble metal of, for example, Au, Cu, Ag, Ru, Rh, Ir, Pt, Pd or the like, or a underlayer of an alloy of any of those noble metals, of an Ni-based alloy layer of NiFe, NiCu, NiFeCr, NiFeTa or the like is provided between the alumina [cap] gap layer and the spin valve film.

IN THE CLAIMS

Claims 1-28 and 34-36 (Canceled).